

REMARKS

The patent owner requests that this preliminary amendment be entered prior to examination of the reissue application of U.S. Patent No. 6,475,846. A drawing amendment is included as a separate paper for Examiner's approval according to 37 CFR 1.173(b)(3). The drawing amendment to Figure 1 changes the Vdd label at the source of transistor 27 to Ground in agreement with the Ground symbol. Two paragraphs from column 4 of the specification are amended to agree with the drawing amendment. No new matter is added.

The Table inserted at column 5, line 16, was a part of the original specification and appears in the electronic copy of the instant specification on the USPTO web site. The Table, however, was inadvertently omitted from the printed specification by the USPTO. The patent owner believes the Table is important to understanding the present invention and, therefore, respectfully requests that the Table be included with the reissued patent.

Claims 1, 4, and 6-8 are amended. New claims 11-65 are added. The patent owner believes original claims 1-10, as amended, and new claims 11-22 are patentable. Claims 1-10, as amended, recite "forming first and second opposite-conductivity-type diffusion regions *at a first time* in said semiconductor body . . . forming first and second same-conductivity-type diffusion regions *at a second time* in said semiconductor body." Support for these amendments is found in Figures 3a and 3c, respectively, and relevant text at column 5, line 32 through column 6, line 4.

New claims 11-12 depend from claim 1 and include limitations that were originally included in original claim 1. New claims 13-23 include limitations shown at Figures 3a-3k and described in relevant text of the instant specification. No new matter is added. Thus, the patent owner believes claims 11-23 are patentable.

New claims 24-44 recite "*simultaneously forming first and second diffusion regions having a second conductivity type in said semiconductor body, said second conductivity type*

being opposite said first conductivity type; *simultaneously forming third and fourth diffusion regions* having said first conductivity type in said semiconductor body, said third diffusion isolated from said semiconductor body by said first diffusion region, said fourth diffusion region separate from said first and second diffusion regions; *forming at least one memory cell in and on said third diffusion region; forming at least one logic transistor having a channel in said second diffusion region; and forming at least another logic transistor having a channel in said fourth diffusion region.*” (emphasis added). Support for these elements is found at Figures 3a-3k and relevant text of the instant specification. None of the references of record disclose these limitations.

New claims 45-65 recite “*forming first and second diffusion regions having a first concentration at a first depth* and having a second conductivity type in said semiconductor body, said second conductivity type being opposite said first conductivity type; *forming third and fourth diffusion regions having a second concentration at a second depth* and having said first conductivity type in said semiconductor body, said third diffusion region isolated from said semiconductor body by said first diffusion region, said fourth diffusion region separate from said first and second diffusion regions; *forming at least one memory cell in and on said third diffusion region; forming at least one logic transistor having a channel in said second diffusion region; and forming at least another logic transistor having a channel in said fourth diffusion region.*” (emphasis added). Support for these elements is found at Figures 3a-3k and relevant text of the instant specification. None of the references of record disclose these limitations.

In view of the foregoing, the patent owner believes that claims 1-65 are allowable. The patent owner requests entry of the preliminary amendment prior to examination and reissue of U.S. Patent No. 6,475,846, with claims 1-65. If the Examiner finds any issue that is unresolved, please call the patent owner's attorney by dialing the telephone number printed below.

Respectfully submitted,

A handwritten signature in black ink, reading "Robert N. Rountree". The signature is fluid and cursive, with the first name "Robert" being more prominent and the last name "Rountree" following in a similar style.

Robert N. Rountree
Attorney for Patent Owner
Reg. No. 39,347

Robert N. Rountree, LLC
70360 Highway 69
Cotopaxi, Colorado 81223
PHONE/FAX: (719) 783-0990